

FORM PTO-1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
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**06413 USA**

SERIAL NO.

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use several sheets if necessary)APPLICANT  
**Hoshang Subawalla, et al.**

FILING DATE

GROUP

(37 CFR 1.98(b))

**U.S. PATENT DOCUMENTS**

EXAM- INE R INITIAL		DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		4	9	9	2	3	0	8	2/12/1991	A. K. Sunol	427	297	9/16/1988
		4	9	4	4	8	3	7	7/31/1990	M. Nishikawa, et al.	156	646	2/28/1989
		5	0	1	3	3	6	6	5/7/1991	D. P. Jackson, et al.	134	1	12/7/1988
		5	1	5	8	7	0	4	10/27/1992	J. L. Fulton, et al.	252	309	7/25/1990
		5	2	6	6	2	0	5	11/30/1993	J. L. Fulton, et al.	210	639	7/1/1992
		5	2	3	6	6	0	2	8/17/1993	D. P. Jackson	210	748	1/28/1991
		5	3	7	7	7	0	5	1/3/1995	C. W. Smith, Jr., et al.	134	95.3	9/16/1993
		5	3	5	5	9	0	1	10/18/1994	R. J. Mielnik, et al.	134	105	10/27/1992
		5	4	9	4	5	2	6	2/27/1996	A. P. Paranjpe	134	1	5/4/1995
		5	4	1	7	7	6	8	5/23/1995	C. W. Smith, Jr., et al.	134	10	12/14/1993
		5	5	3	3	5	3	8	7/9/1996	M. C. Marshall	134	104.4	12/1/1994
		5	5	2	2	9	3	8	6/4/1996	S. O'Brien	134	1	8/8/1994
		5	7	8	9	5	0	5	8/4/1998	S. P. Wilkinson, et al.	526	209	8/14/1997
		5	7	8	3	0	8	2	7/21/1998	J. M. DeSimone, et al.	210	634	11/3/1995
		5	7	3	3	9	6	4	3/31/1998	K. P. Johnston, et al.	524	505	6/20/1996
		5	8	7	3	9	4	8	2/23/1999	J-J Kim	134	19	6/24/1997
		5	8	7	2	2	5	7	2/16/1999	E. J. Beckman, et al.	546	336	4/1/1997
		5	8	6	8	8	5	6	2/9/1999	M. A. Douglas, et al.	134	2	7/23/1997
		5	8	6	6	0	0	5	2/2/1999	J. M. DeSimone, et al.	210	634	11/1/1996
		5	9	7	6	2	6	4	11/2/1999	K. J. McCullough, et al.	134	2	11/30/1998
		5	9	4	4	9	9	6	8/31/1999	J. M. DeSimone, et al.	210	634	5/2/1997
		5	9	0	8	5	1	0	6/1/1999	K. J. McCullough, et al.	134	2	10/16/1996
		6	0	2	4	8	0	1	2/15/2000	R. M. Wallace, et al.	134	1	12/9/1996
		6	1	7	6	8	9	5	1/23/2001	J. M. DeSimone, et al.	75	723	11/4/1998
		6	1	1	3	7	0	8	9/5/2000	G. B. Hopple, et al.	134	7	5/26/1998
		6	2	9	7	2	0	6	10/2/2001	T. J. Romack, et al.	510	285	1/23/2001
		6	2	7	7	7	5	3	8/21/2001	W. H. Mullee, et al.	438	692	9/28/1999
		6	2	7	0	5	3	1	8/7/2001	J. P. DeYoung, et al.	8	142	8/28/1998
		6	2	4	2	1	6	5	6/5/2001	B. A. Vaartstra	430	329	8/28/1998
		6	2	4	0	9	3	6	6/5/2001	J. M. DeSimone, et al.	134	33	1/22/1999
		6	2	2	8	5	6	3	5/8/2001	V. Starov, et al.	430	327	9/17/1999
		6	2	2	4	7	7	4	5/1/2001	J. M. DeSimone, et al.	210	634	2/12/1999
		6	3	4	4	2	4	3	2/5/2002	J. B. McClain, et al.	427	388.1	8/2/2001
		6	3	3	3	2	6	8	12/25/2001	V. Starov, et al.	438	691	8/1/2000
		6	3	3	1	4	8	7	12/18/2001	R. Koch	438	692	2/27/2001
		6	3	0	6	5	6	4	10/23/2001	W. H. Mullee	430	329	5/27/1998
		6	4	5	4	8	6	9	9/24/2002	J. M. Cotte, et al.	134	2	6/27/2001
		6	4	0	3	5	4	4	6/11/2002	L. B. Davenport, et al.	510	175	7/21/2000
		6	5	0	0	6	0	5	12/31/2002	W. H. Mullee, et al.	430	329	10/25/2000
		6	5	0	6	2	5	9	1/14/2003	T. J. Romack, et al.	134	10	11/20/2000
		6	5	0	6	2	5	9	1/14/2003	T. J. Romack, et al.	134	10	11/20/2000
	2002	0	0	8	8	4	7	7	7/11/2002	J. M. Cotte, et al.	134	2	1/5/2001
	2002	0	1	1	2	7	4	7	8/22/2002	J. P. DeYoung, et al.	134	36	9/13/2001
	2003	0	0	0	3	7	6	2	1/2/2003	J. M. Cotte, et al.	438	745	6/27/2001

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
													YES	NO
	EP	0	8	3	6	8	9	5		Europe			X	
	WO	00	0	1	6	2	6	4		World			X	
	WO	00	0	2	6	4	2	1		World			X	
	WO	01	0	2	1	6	1	6		World			X	

# **FOREIGN PATENT DOCUMENTS**

WO	01	0	3	3	6	1	3		World			X	
WO	01	0	3	2	3	2	3		World			X	
WO	01	0	8	7	5	0	5		World			X	
WO	02	0	1	1	1	9	1		World			X	
WO	02	0	1	5	2	5	1		World			X	
WO	02	0	6	6	1	7	6		World			X	
WO	99	0	4	9	9	9	8		World			X	
WO	99	0	4	9	9	9	6		World			X	

## **OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

			K. Jackson, et al., "Microemulsions in Supercritical Hydrochlorofluorocarbons," Langmuir 12(22), pp. 5289-5295 (1996).										
			M. A. Biberger, et al., "Photoresist and Photoresist Residue Removal with Supercritical CO <sub>2</sub> – A Novel Approach to Cleaning Wafers," Semiconductor Fabtech, 12 <sup>th</sup> Ed., pp. 239-243.										
			D. Beery, et al., "Post Etch Residue Removal: Novel Dry Clean Technology Using Densified Fluid Cleaning (DFC)," IITC 99, pp. 140-142.										
			J. Liu, et al., "Investigation of Nonionic Surfactant Dynol-604 Based Reverse Microemulsions Formed in Supercritical Carbon Dioxide," Langmuir 17, pp. 8040-8043 (2001).										
			K. Jackson, et al., "Surfactants and Microemulsions in Supercritical Fluids," Supercritical Fluid Cleaning, pp. 87- 120.										
			R. A. Bowling, et al., "Future Challenges for Cleaning in Advanced Microelectronics," Texas Instruments slides.										
			H. J. Martinez, et al., "SCCO <sub>2</sub> – Is it an Enabling Technology for the 90nm Node and Beyond?" International SeMatech slides (2002).										
			S. Pawat, "Novel Wafer Clean Technologies," International SeMatech slides (2001).										
			T. Hurd, et al., "scCO <sub>2</sub> Cleaning Applications in Porous ULK Processing," Texas Instruments slides.										
			G. L. Weibel, et al., "Supercritical CO <sub>2</sub> in Microelectronics Processing," Cornell University slides.										
			J. B. Rubin, et al., "Precision Cleaning of Semiconductor Surfaces Using Carbon Dioxide-Based Fluids," Clarkson University, pp. 1-26.										
			G. Weibel, "Supercritical CO <sub>2</sub> for Semiconductor Applications," Semiconductor Equipment and Materials International (2001).										
			J. Malloy, et al., "GC Analysis of Solvent Wash Samples," Air Products and Chemicals, Inc. (2003).										

EXAMINER	DATE CONSIDERED
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**EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.**